



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D.C. 20231
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/607,922	06/30/2000	William Frederick Bosch	015290-426	9687

21839 7590 08/13/2002

BURNS DOANE SWECKER & MATHIS L L P
POST OFFICE BOX 1404
ALEXANDRIA, VA 22313-1404

EXAMINER

UMEZ ERONINI, LYNETTE T

ART UNIT	PAPER NUMBER
----------	--------------

1765

DATE MAILED: 08/13/2002

17

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/607,922

Applicant(s)

BOSCH, WILLIAM FREDERICK

Examiner

Lynette T. Umez-Eronini

Art Unit

1765

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☐ Responsive to communication(s) filed on ____.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-30 is/are pending in the application.
- 4a) Of the above claim(s) ____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) ____ is/are allowed.
- 6) ☒ Claim(s) 1-30 is/are rejected.
- 7) ☐ Claim(s) ____ is/are objected to.
- 8) ☐ Claim(s) ____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on ____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on ____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. ____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☐ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 10, 12 & 16
- 4) ☐ Interview Summary (PTO-413) Paper No(s) ____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: ____

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claims 15-17 and 19-30 rejected under 35 U.S.C. 102(b) as being anticipated by Schoepp et al. (WO 99/50886).

Schoepp teaches a method of plasma conditioning a sintered surface of a ceramic part of a semiconductor processing chamber, the part being made of a ceramic material, the method comprising treating a sintered SiC surface and reducing particle contamination by supplying process gas to the processing chamber (page 2, lines 13-15 and page 3, line 8-9) and energizing the process gas into a plasma that comprises high density plasma (page 2, line 28 - page 3, line 8) with a chamber pressure below 300mTorr, antenna power at 200-5000 watts, and process gas that includes CHF₃, C₂HF₅ and or C₂F₆ (page 10, lines 11-15).

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

4. Claim 18 is rejected under 35 U.S.C. 103(a) as being unpatentable over Schoepp (WO '886) as applied to claim 15 above, and further in view of Wicker (US 5,863,376).

Schoepp differs in failing to teach recited process variables such as pressure of 200 to 500 mTorr and radio frequency power of 2000 to 25000 W, in claim 18.

Wicker teaches a vacuum pressure at below 300 mTorr and radio frequency bias at less than 2200 watts (column 5, lines 59-61).

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Schoepp by using the processing variables as taught by Wicker for the purpose of

5. Claims 1, 2, 3, 6, 7, 8, 9, 10, 11, 13, 14, and 31-34 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lu et al. (US 5,904,778) as applied in view of Schoepp (WO '886).

Lu teaches a method of processing semiconductor substrates and reducing particle contamination during processing of the substrate, the method comprising the steps of:

loading a wafer that is supported on a pedestal in a vacuum (high density plasma oxide etcher) chamber that is made of silicon carbide (Figure 1; column 1, lines 20, 21, 24-27, and 36-40; Table 4; column 9, line 61 – column 10, line 24; and column 11, line 59 - column 12, line 5);

etching the wafer (silicon oxide overlying silicon or polysilicon and CVD SiC materials which can be applied to complex shapes) samples with a fluorocarbon plasma (column 1, lines 53-58 and column 7, lines 4-6, 53 and 54), reads on,

(a) placing at least one substrate on a substrate holder in an interior space of a vacuum processing chamber, the processing chamber including at least one non-oxide ceramic part having a surface exposed to the interior space;

(b) processing the at least one substrate by supplying process gas to the processing chamber; and

inspecting these samples by a microscope after etching (Abstract; column 7, lines 22-24 and 40-45), which suggests

(c) removing the at least one substrate from the processing chamber.

Lu differs in failing to teach the processing chamber including at least one ceramic part made of a non-oxide ceramic material, and having a machined and/or sintered surface exposed to the interior space, the exposed surface having been treated to reduce particles of the non-oxide ceramic material attached to the exposed surface by a high intensity plasma conditioning treatment, in claims 1, 32 and 34.

Schoepp teaches a method of processing a substrate that the comprises a sintered SiC surface and reducing particle contamination by supplying process gas to the processing chamber (page 2, lines 13-15 and page 3, line 8-9) and energizing the process gas into a plasma that comprises high density plasma (page 2, line 28 - page 3, line 8), which reads on, the processing chamber including at least one ceramic part made of a non-oxide ceramic material and having a sintered surface exposed to the

Art Unit: 1765

interior space, the exposed surface having been treated to reduce particles of the non-oxide ceramic material attached to the exposed surface by a high intensity plasma conditioning treatment.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Lu by using Schoepp's method of treating a non-oxide ceramic material that has a sintered surface for the purpose of providing improvements in reducing contamination of substrates (Schoepp, page 5, lines 21-23).

6. Claims 4, 5, and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lu (US '778) in view of Schoepp (WO '886) as applied to claim 1 above, and further in view of Wicker et al. (US 5,863,376).

treatment of the exposed surface with an oxygen gas into a plasma state, **in claim 12.**

recited process variables such as pressure of 200 to 500 mTorr and radio frequency power of 2000 to 25000 W, **in claims 4;** and

sequential treatment of no more than 50 wafers in the processing chamber, **in claim 5.**

Wicker teaches vacuum plasma processing chamber comprising:

a process of etching the wafers followed by ashing with O₂ (column 5, lines 13-1518), which reads on treating the exposed surface with an oxygen gas is a plasma state;

Art Unit: 1765

a vacuum pressure at below 300 mTorr and radio frequency bias at less than 2200 watts (column 5, lines 59-61); and

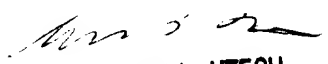
a sequential method of processing of 25 wafers in the chamber (column 5, lines 5 and 6).

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Lu in view Schoepp by using oxygen gas in the processing chamber, the process parameters, and sequential treatment of no more than 50 wafers in the processing chamber as taught by Wicker for the purpose of minimizing the degradation of the quality of the processed substrate during sequential batch processing of substrates (Abstract).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lynette T. Umez-Eronini whose telephone number is 703-306-9074. The examiner can normally be reached on Second Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Benjamin Utech can be reached on 703-308-3836. The fax phone numbers for the organization where this application or proceeding is assigned are 703-972-9310 for regular communications and 703-972-9311 for After Final communications.

ltue
August 12, 2002


BENJAMIN L. UTECH
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 1700